





#### 180V NPN SMALL SIGNAL TRANSISTOR IN SOT323

#### **Features**

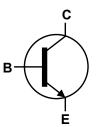
- Epitaxial Planar Die Construction
- Ultra-Small Surface Mount Package
- Complementary NPN Type: MMST5401
- Ideal for Low Power Amplification and Switching
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

### **Mechanical Data**

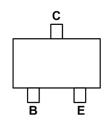
- Case: SOT323
- Case Material: Molded Plastic. "Green" Molding Compound.
   UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 <sup>3</sup>
- Weight: 0.006 grams (approximate)







Device Symbol



Top View Pin-Out

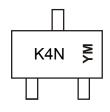
### Ordering Information (Notes 4 & 5)

| Device        | Compliance | Marking | Reel Size (inches) | Tape Width (mm) | Quantity per reel |
|---------------|------------|---------|--------------------|-----------------|-------------------|
| MMST5551-7-F  | AEC-Q101   | K4N     | 7                  | 8               | 3,000             |
| MMST5551Q-7-F | Automotive | K4N     | 7                  | 8               | 3,000             |

#### Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product\_compliance\_definitions/.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## Marking Information



K4N = Product Type Marking Code YM = Date Code Marking Y or  $\underline{Y}$  = Year (ex: A = 2013) M or  $\underline{M}$  = Month (ex: 9 = September)

#### Date Code Key

| Date Code ite |      |     |      |      |     |      |      |     |      |      |     |      |
|---------------|------|-----|------|------|-----|------|------|-----|------|------|-----|------|
| Year          | 2010 |     | 2011 | 2012 |     | 2013 | 2014 |     | 2015 | 2016 |     | 2017 |
| Code          | X    |     | Υ    | Z    |     | Α    | В    |     | С    | D    |     | E    |
| Month         | Jan  | Feb | Mar  | Apr  | May | Jun  | Jul  | Aug | Sep  | Oct  | Nov | Dec  |
| Code          | 1    | 2   | 3    | 4    | 5   | 6    | 7    | 8   | 9    | 0    | N   | D    |



# **Absolute Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic               | Symbol           | Value | Unit |
|------------------------------|------------------|-------|------|
| Collector-Base Voltage       | $V_{CBO}$        | 180   | V    |
| Collector-Emitter Voltage    | $V_{\sf CEO}$    | 160   | V    |
| Emitter-Base Voltage         | V <sub>EBO</sub> | 6.0   | V    |
| Continuous Collector Current | Ic               | 200   | mA   |

### Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic                                   |                 | Symbol           | Value | Unit |
|--|-----------------|------------------|-------|------|
| Power Dissipation                                | (Note 6)        | $P_{D}$          | 200   | mW   |
| Thermal Resistance, Junction to Ambient (Note 6) |                 | R <sub>0JA</sub> | 625   | °C/W |
| Operating and Storage Temperature Range          | $T_{J,}T_{STG}$ | -55 to +150      | °C    |      |

### ESD Ratings (Note 7)

| Characteristic                             | Symbol  | Value | Unit | JEDEC Class |
|--|---------|-------|------|-------------|
| Electrostatic Discharge - Human Body Model | ESD HBM | 4,000 | V    | 3A          |
| Electrostatic Discharge - Machine Model    | ESD MM  | 400   | V    | С           |

# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic                       | Symbol                       | Min      | Max  | Unit | Test Condition   |  |
|--------------------------------------|------------------------------|----------|------|------|--|--|
| OFF CHARACTERISTICS (Note 8)         | DFF CHARACTERISTICS (Note 8) |          |      |      |  |  |
| Collector-Base Breakdown Voltage     | V <sub>CBO</sub>             | 180      | _    | V    | $I_{C} = 100 \mu A, I_{E} = 0$   |  |
| Collector-Emitter Breakdown Voltage  | $V_{CEO}$                    | 160      | _    | V    | $I_C = 1.0 \text{mA}, I_B = 0$   |  |
| Emitter-Base Breakdown Voltage       | V <sub>EBO</sub>             | 6.0      | _    | V    | $I_E = 10\mu A, I_C = 0$   |  |
| Collector Cutoff Current             | 1                            |          | 50   | nA   | V <sub>CB</sub> = 120V, I <sub>E</sub> = 0   |  |
| Collector Cutoff Current             | I <sub>CBO</sub>             | _        | 30   | μΑ   | $V_{CB} = 120V$ , $I_{E} = 0$ , $T_{A} = +100$ °C  |  |
| Emitter Cutoff Current               | I <sub>EBO</sub>             | _        | 50   | nA   | $V_{EB} = 4.0V, I_C = 0$   |  |
| ON CHARACTERISTICS (Note 8)          |                              |          |      |      |  |  |
|                                      |                              | 80       | _    |      | $I_C = 1.0 \text{mA}$ , $V_{CE} = 5.0 \text{V}$  |  |
| DC Current Gain                      | h <sub>FE</sub>              | 80<br>30 | 250  | _    | $I_C = 10 \text{mA}, V_{CE} = 5.0 \text{V}$  |  |
|                                      |                              | 30       | 0.15 |      | $I_C = 50 \text{mA}, V_{CE} = 5.0 \text{V}$<br>$I_C = 10 \text{mA}, I_B = 1.0 \text{mA}$ |  |
| Collector-Emitter Saturation Voltage | V <sub>CE(SAT)</sub>         | _        | 0.20 | V    | $I_{\rm C} = 50  \text{mA}, I_{\rm B} = 5.0  \text{mA}$                                  |  |
| Base-Emitter Saturation Voltage      | V <sub>BE(SAT)</sub>         | _        | 1.0  | V    | $I_C = 10mA, I_B = 1.0mA$  |  |
|                                      | V BE(SAT)                    |          | 1.0  |      | $I_{\rm C} = 50 \text{mA}, I_{\rm B} = 5.0 \text{mA}$                                    |  |
| SMALL SIGNAL CHARACTERISTICS         |                              |          |      | ,    |  |  |
| Output Capacitance                   | C <sub>obo</sub>             | _        | 6.0  | pF   | $V_{CB} = -10V$ , $f = 1.0MHz$ , $I_E = 0$   |  |
| Small Signal Current Gain            | h <sub>fe</sub>              | 50       | 250  | _    | $V_{CE} = 10V, I_{C} = 1.0mA,$   |  |
| oman dignar danting dant             | riie                         |          | 200  |      | f = 1.0kHz   |  |
| Current Gain-Bandwidth Product       | f <sub>T</sub>               | 100      | 300  | MHz  | $V_{CE} = 10V, I_{C} = 10mA,$<br>f = 100MHz  |  |
| Noise Figure                         | NF                           | _        | 8.0  | dB   | $V_{CE}$ = 5.0V, $I_{C}$ = 200 $\mu$ A, $R_{S}$ =1.0 $\Omega$ , $f$ = 1.0kHz             |  |

Notes:

- 6. For a device mounted on minimum recommended pad layout 1oz copper that is on a single-sided FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
- 7. Refer to JEDEC specification JESD22-A114 and JESD22-A115.
- 8. Measured under pulsed conditions. Pulse width  $\leq$  300µs. Duty cycle  $\leq$  2%.



## Typical Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

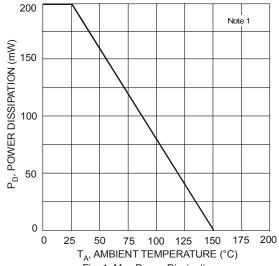
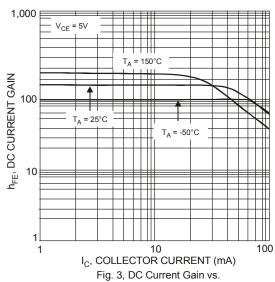
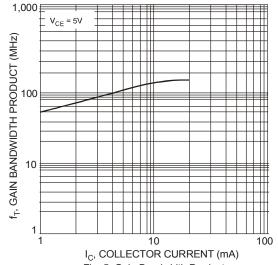


Fig. 1, Max Power Dissipation vs.
Ambient Temperature





Collector Current

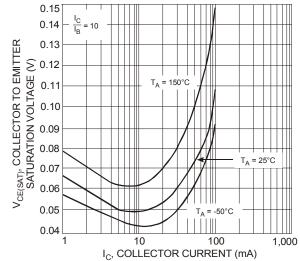
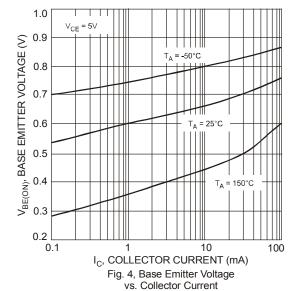


Fig. 2, Collector Emitter Saturation Voltage vs. Collector Current

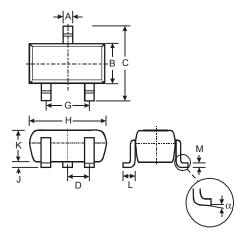


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# **Package Outline Dimensions**

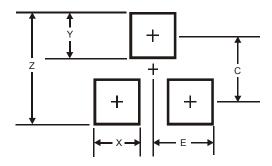
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



|                      | SOT323 |      |      |  |  |  |  |
|----------------------|--------|------|------|--|--|--|--|
| Dim                  | Min    | Max  | Тур  |  |  |  |  |
| Α                    | 0.25   | 0.40 | 0.30 |  |  |  |  |
| В                    | 1.15   | 1.35 | 1.30 |  |  |  |  |
| C                    | 2.00   | 2.20 | 2.10 |  |  |  |  |
| D                    | -      | -    | 0.65 |  |  |  |  |
| G                    | 1.20   | 1.40 | 1.30 |  |  |  |  |
| Н                    | 1.80   | 2.20 | 2.15 |  |  |  |  |
| 7                    | 0.0    | 0.10 | 0.05 |  |  |  |  |
| K                    | 0.90   | 1.00 | 1.00 |  |  |  |  |
| L                    | 0.25   | 0.40 | 0.30 |  |  |  |  |
| M                    | 0.10   | 0.18 | 0.11 |  |  |  |  |
| α                    | 0°     | 8°   | -    |  |  |  |  |
| All Dimensions in mm |        |      |      |  |  |  |  |

## **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



| Dimensions | Value (in mm) |
|------------|---------------|
| Z          | 2.8           |
| Х          | 0.7           |
| Y          | 0.9           |
| С          | 1.9           |
| F          | 1.0           |

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device Terminals and PCB tracking.

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